

QuikPAC Module Data

QPP-012 120W, 925-960MHz Class AB Power Stage

General description:

The QPP-012 QuikPACTM RF power module is a Class AB amplifier stage designed for use in the output stage of linear RF power amplifiers for cellular base stations. The power transistors are fabricated using Xemod's advanced design LDMOS process. This unit has a factory set, regulated and temperature compensated gate bias, eliminating the need for the user to provide adjustable gate bias voltage circuits and make individual bias adjustments during stage alignment.

Features:

Single Polarity Operation
Matched for 50 Ω RF interfaces
XeMOS FET Technology
Stable Performance
QuikPAC System Compatible
QuikClip or Flange Mounting

Standard Operating Conditions

| Parameter | Symbol | Min | Nom | Max | Units |
|--|-----------------|------|------|------|-------|
| Frequency Range | F | 925 | | 960 | MHz |
| Supply (Drain) Voltage | V_D | 26.0 | 28.0 | 32.0 | VDC |
| Bias (Gate) Voltage | V_{G} | 11.0 | 12.0 | 13.0 | VDC |
| Bias (Gate) Current, Average | I_{G} | | | 40 | mA |
| RF Source & Load Impedance | Ω | | 50 | | Ohms |
| Load Impedance for Stable Operation (All Phases) | VSWR | | | 10:1 | |
| Operating Baseplate Temperature | T _{OP} | -20 | | +90 | °C |
| Output Device Thermal Resistance, Channel to Baseplate | Θјс | | 0.8 | | °C/W |

Maximum Ratings

| Parameter | Symbol | Value | Units |
|--|------------------|-------------|-------|
| Supply (Drain) Voltage | V_{DD} | 35 | VDC |
| Control (Gate) Voltage, V _{DD} = 0 VDC | V_{G} | 15 | VDC |
| Input RF Power | P _{IN} | 60 | W |
| Load Impedance for continuous operation without damage | VSWR | 3:1 | |
| Output Device Channel Temperature | | 200 | °C |
| Lead Temperature During Reflow Soldering | | +210 | °C |
| Storage Temperature | T _{STG} | -40 to +100 | °C |

Performance at 28VDC & 25°C

| Parameter | Symbol | Min | Nom | Max | Units |
|--|-----------------|------|-------|-------|-------|
| Supply (Drain) Voltage | $V_{D1,2}$ | 27.5 | 28.0 | 28.5 | VDC |
| Quiescent Current (total) (1) | I_{DQ} | 900 | 1,000 | 1,100 | mA |
| Power Output at 1 dB Compression (single tone) | P ₋₁ | 120 | 130 | | W |
| Gain at 120W PEP (two tone) | G | 12.0 | 13.0 | | dB |
| Gain Variation over frequency at 120W Output (two tone) | ΔG | | 0.3 | 0.5 | dB |
| Input Return Loss (50 Ω Ref) at 120W PEP (two tone) | IRL | 12.0 | 14.0 | | dB |
| Drain Efficiency at 120W P _{out} (single tone) | η | 40 | 45 | | % |
| Drain Efficiency at 120W PEP (two tone) | η | 32 | 33 | | % |
| 3 rd Order IMD Product (2 tone at 120W PEP;1 MHz spacing) | | | -28 | -26 | dBc |

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Performance at 28VDC & 25°C (continued)

| Parameter | Symbol | Min | Nom | Max | Units |
|---|-----------|-----|-----|-----|---------|
| IMD Variation – 100 kHz to 25 MHz tone spacing | | | 1.0 | 2.0 | dB |
| 2 nd Harmonic at 120W P _{out} (single tone) | | | | | dBc |
| 3 rd Harmonic at 120W P _{out} (single tone) | | | | | dBc |
| Group (Signal) Delay | $	au_{d}$ | | 4.0 | | ns |
| Transmission Phase Flatness | | | 0.5 | | degrees |

Performance at 28VDC Over Temperature

| Parameter | Symbol | Min | Nom | Max | Units |
|--|-----------------|-----|-----|-----|-------|
| Power Output at 1 dB Compression (single tone) | P ₋₁ | | | | W |
| Gain Variation over frequency at 24W Output (single tone) | ΔG | | | | dB |
| Input Return Loss (50 Ω Ref) at 24W PEP (two tone) | IRL | | | | dB |
| Drain Efficiency at 120W PEP (two tone) | η | | | | % |
| 3 rd Order IMD Product (2 tone at 120W PEP;1 MHz spacing) | | | 4.0 | | dBc |
| Group (Signal) Delay | $	au_{d}$ | | 0.5 | | ns |

Notes:

This GR-version QuikPAC module has an internally regulated gate voltage that is preset at the factory. A voltage of +12VDC (±1V) should be applied to each gate lead (pins 1 and 5). No further adjustment is required. The gate voltage is thermally compensated for operation over the temperature range listed in the data sheet. Although the module will operate with lower voltages applied, the internal regulator is not functioning and the specified performance may not be achieved.

Gate voltage must be applied coincident with or after application of the drain voltage to prevent potentially destructive oscillations. Bias voltages should never be applied to a module unless it is terminated on both input and output.

The quiescent current set during manufacture will be within the range specified in the Performance section (nominal $\pm 10\%$) and is selected to balance IMD, input return loss, and efficiency. This setting is suitable for most applications. Modules with different optimization profiles are available by special order.

Internal RF decoupling is included on all bias leads. No additional bypass elements are required, however some applications may require energy storage on the drain leads to accommodate time-varying waveforms.

The RF leads are internally protected against DC voltages up to 100V. Care should be taken to avoid video transients that may damage the active devices.

Package Styles

This model is available in both B2 (H10537) and B2F (H10894) package styles. Style B2F is shown for reference. Please see the applicable outline drawing for specific dimensions.

